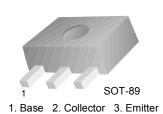
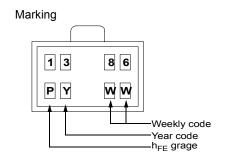


# FJC1386 PNP Epitaxial Silicon Transistor

## **Low Saturation Transistor Medium Power Amplifier**

- Complement to FJC2098
- · High Collector Current
- · Low Collector-Emitter Saturation Voltage





## Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub> Collector-Base Voltage		-30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-20	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current (DC)	-5	Α
P <sub>C</sub>	Power Dissipation (T <sub>a</sub> = 25°C)	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C

#### Electrical Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -50\mu A, I_E = 0$	-30		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = -1 \text{mA}, I_{B} = 0$	-20		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -50\mu A, I_C = 0$	-6		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = -20V, V_{B} = 0$		-0.5	μΑ
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = -5V, I_{C} = 0$		-0.5	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -2V, I_{C} = -0.5A$	80	390	
V <sub>CE (sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = -4A, I_B = -0.1A$		-1.0	V
V <sub>BE (sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -4A, I <sub>B</sub> = -0.1A		-1.5	V

## Thermal Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

## h<sub>FE</sub> Classification

Classification	Р	Q	R
hFE	80 ~ 180	120 ~ 270	180 ~ 390

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1386	FJC1386	SOT-89	13"		4,000

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

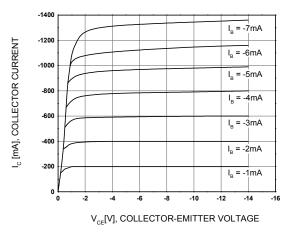
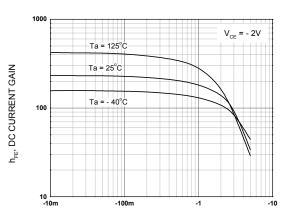


Figure 2. DC Current Gain



 $I_{\rm c}$  [A], COLLECTOR CURRENT

Figure 3. Collector-Emitter Saturation Voltage

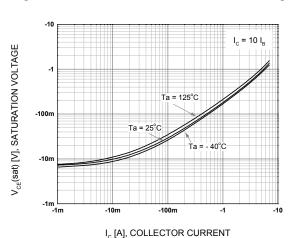


Figure 4. Base-Emitter Saturation Voltage

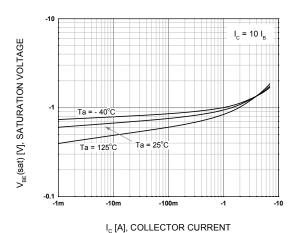


Figure 5. Base-Emitter On Voltage

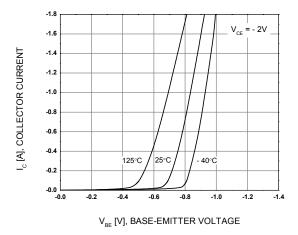
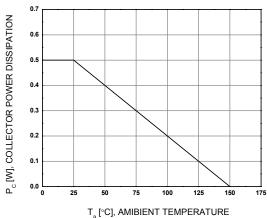
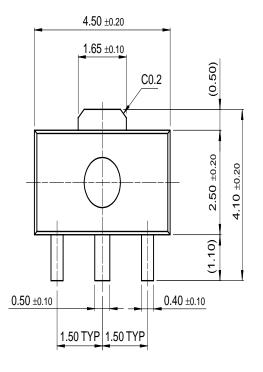


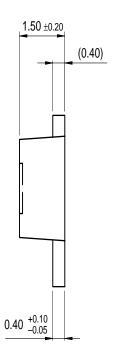
Figure 6. Power Derating

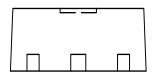


## **Mechanical Dimensions**

# **SOT-89**







Dimensions in Millimeters

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SuperSOT™-3

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#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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